L Number	Hits	Search Text	DB	Time stamp
1	15	finfet	EPO; JPO; DERWENT; IBM_TDB	2004/06/08 11:53
2	71	(tri-gate (triple near3 gate) (three near3 gate)) with FET	EPO; JPO; DERWENT; IBM_TDB	2004/06/08 11:55
3	23117	SOI (silicon near3 insulat$3)	EPO; JPO; DERWENT; IBM_TDB	2004/06/08 11:56
4	914	(SOI (silicon near3 insulat$3)) and FET	EPO; JPO; DERWENT; IBM_TDB	2004/06/08 11:57
5	17	((SOI (silicon near3 insulat$3)) and FET) and (stud mesa fin)	EPO; JPO; DERWENT; IBM_TDB	2004/06/08 11:57
6	50717	SOI (silicon near3 insulat$3)	USPAT; US-PGPUB	2004/06/08 11:57
7	6343	(SOI (silicon near3 insulat$3)) and FET	USPAT; US-PGPUB	2004/06/08 11:57
8	860	((SOI (silicon near3 insulat$3)) and FET) and (stud mesa fin)	USPAT; US-PGPUB	2004/06/08 11:58
-	78	finfet	USPAT; US-PGPUB	2004/06/08 11:52
-	78	finfet and gate	USPAT; US-PGPUB	2004/05/05 19:32
-	17	(finfet and gate) and ((tri three triple) near5 gate)	USPAT; US-PGPUB	2004/05/05 19:16
-	14	((finfet and gate) and ((tri three triple) near5 gate)) and (messa recess trench open$4 hole)	USPAT; US-PGPUB	2004/05/05 19:16
-	4	(((finfet and gate) and ((tri three triple) near5 gate)) and (messa recess trench open$4 hole)) and (dummy sacrificial temporary)	USPAT; US-PGPUB	2004/05/05 19:19
-	14	(((finfet and gate) and ((tri three triple) near5 gate)) and (messa recess trench open$4 hole)) and ((SOI (silion near5 insulat$3)) near10 (wafer substrate))	USPAT; US-PGPUB	2004/05/05 19:20
-	4	((((finfet and gate) and ((tri three triple) near5 gate)) and (messa recess trench open$4 hole)) and ((SOI (silion near5 insulat$3)) near10 (wafer substrate))) and (((finfet and gate) and ((tri three triple) near5 gate)) and (messa recess trench open$4 hole)) and (dummy sacrificial temporary))	USPAT; US-PGPUB	2004/05/05 19:20
-	10	finfet	EPO; JPO; DERWENT; IBM_TDB	2004/05/05 19:32
-	7	finfet and gate	EPO; JPO; DERWENT; IBM_TDB	2004/05/05 19:32
-	335	(FINFET FIN?FET (FIN near3 FET) (FIN near3 MOSFET) (FIN near10 transistor))	USPAT; US-PGPUB	2004/05/06 11:54
-	237	((FINFET FIN?FET (FIN near3 FET) (FIN near3 MOSFET) (FIN near10 transistor))) and gate	USPAT; US-PGPUB	2004/05/06 11:54
-	510	(FINFET FIN?FET (FIN near3 FET) (FIN near3 MOSFET) (FIN near10 transistor) (pillar near10 (FET MOSFET)))	USPAT; US-PGPUB	2004/05/06 12:18
-	412	((FINFET FIN?FET (FIN near3 FET) (FIN near3 MOSFET) (FIN near10 transistor) (pillar near10 (FET MOSFET))) and gate	USPAT; US-PGPUB	2004/05/06 12:18
-	333	(FINFET FIN?FET (FIN near3 FET) (FIN near3 MOSFET) (FIN near10 transistor) (pillar near10 (FET MOSFET)))	EPO; JPO; DERWENT; IBM_TDB	2004/05/06 12:18
-	64	((FINFET FIN?FET (FIN near3 FET) (FIN near3 MOSFET) (FIN near10 transistor) (pillar near10 (FET MOSFET)))) and gate	EPO; JPO; DERWENT; IBM_TDB	2004/05/06 12:18